

**Organic Electronic Devices Based on Novel Organics
Containing Diazaborole Rings** **semiconductor**

Supporting Information

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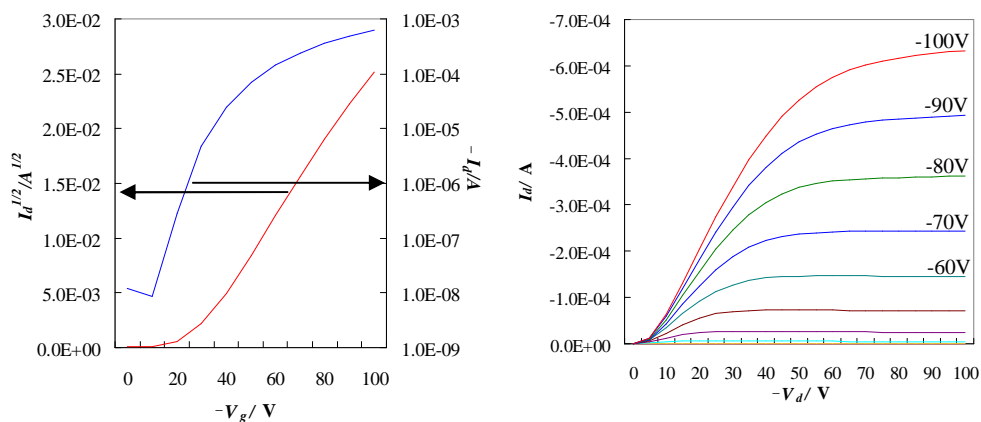
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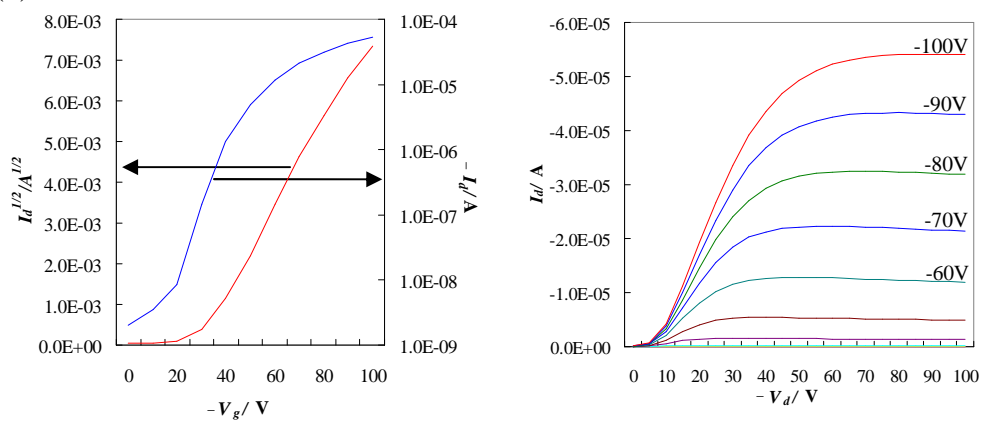
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the bottom-contact FET devices of **2-6**.----- p.3-8

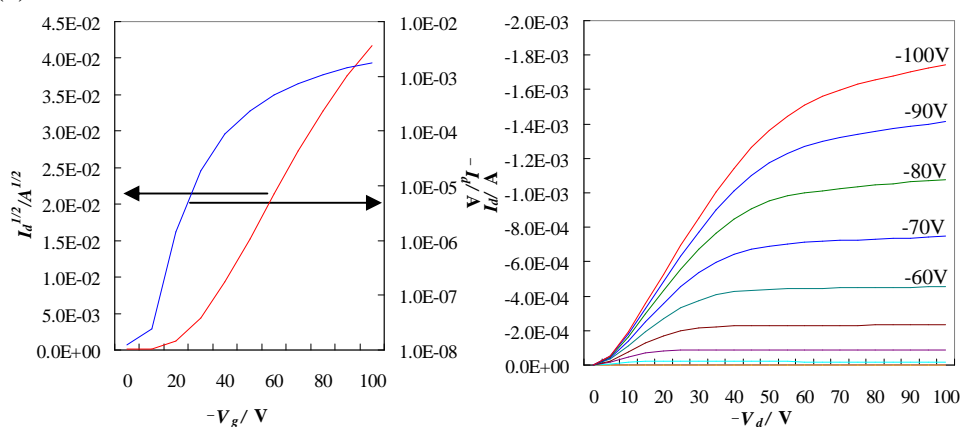
(a)HMDSr.t.



(b)Bare80 °C

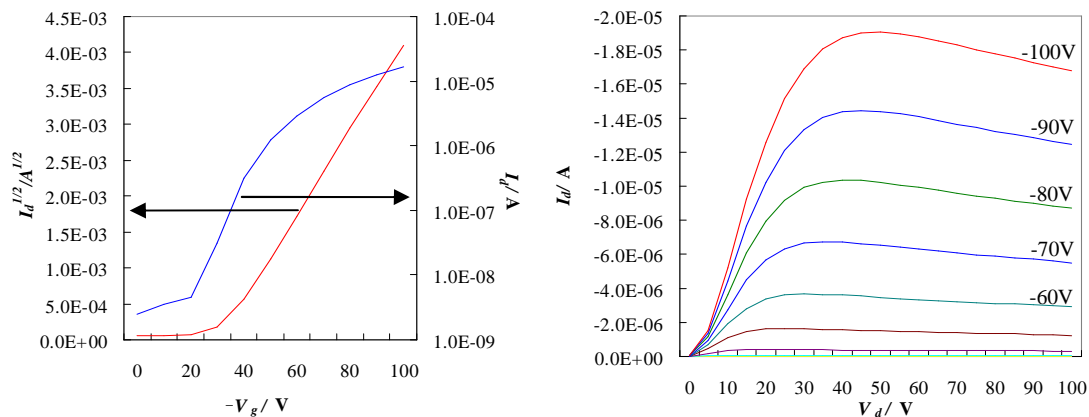


(c)HMDS80 °C



FigureS1. Output and transfer characteristics of the bottom-contact FET devices of **2** deposited on the (a) HMDS treated substrate at r.t., (b) bare substrate at 80 °C and (c) HMDS treated substrate at 80 °C.

(a)Barer.t.



(b)HMDSr.t.

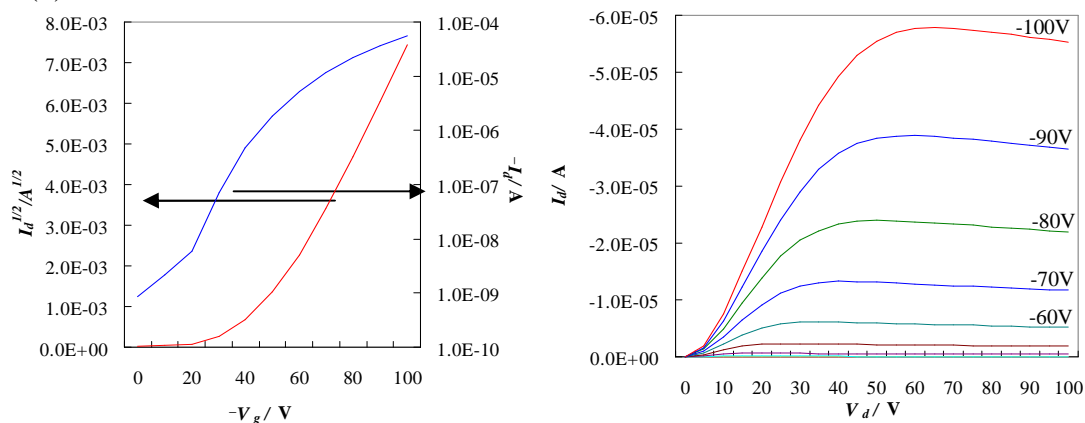
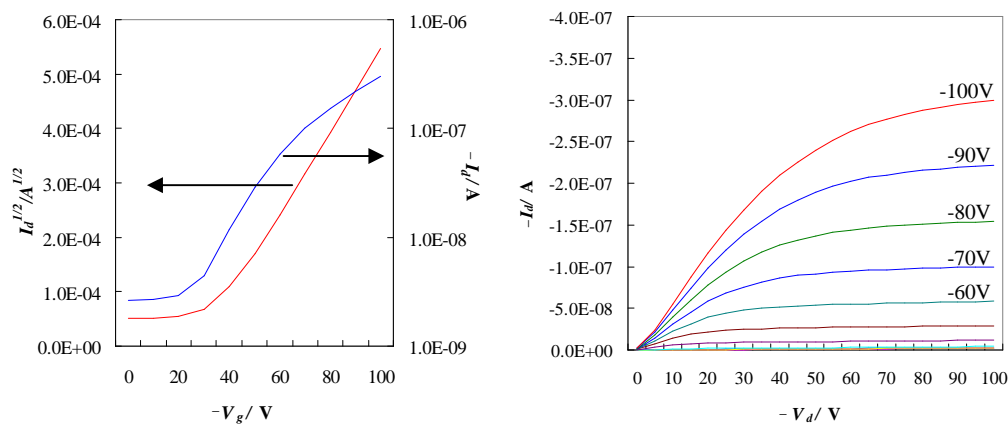


Figure S2. Output and transfer characteristics of the bottom- contact FET devices of **3** deposited on the bare substrate at r.t. (a), HMDS treated substrate at r.t. (b).

(a)Barer.t.



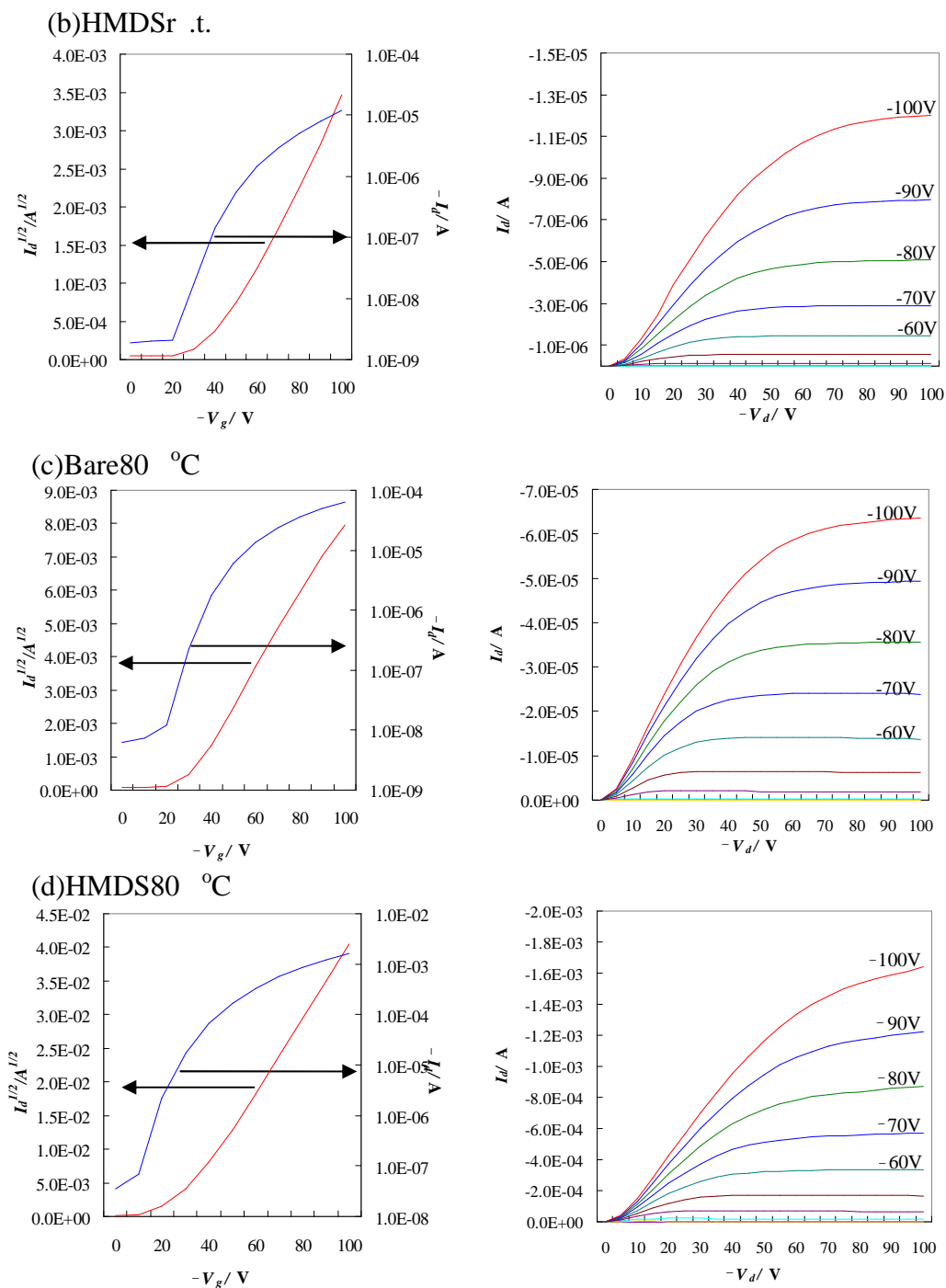
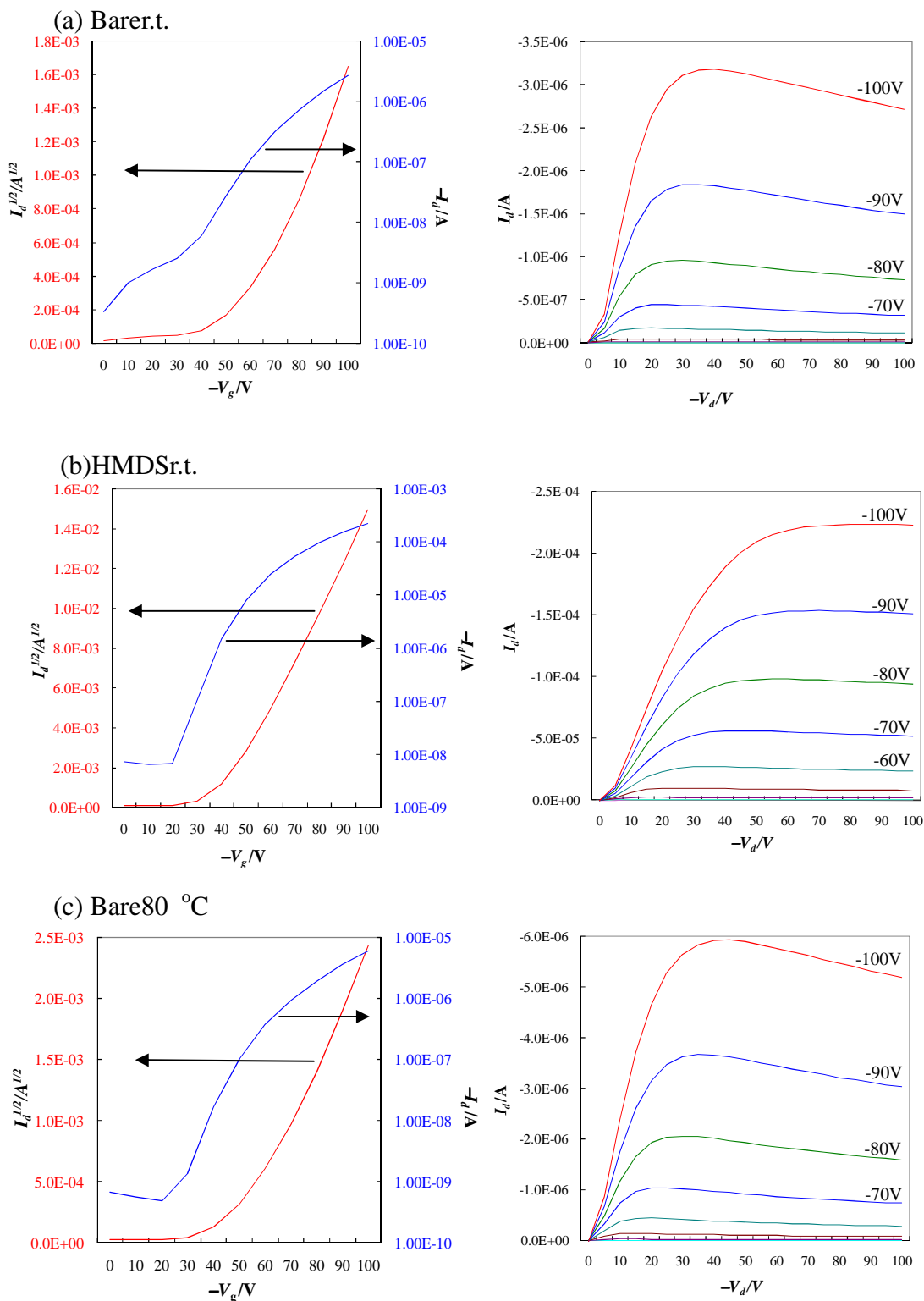
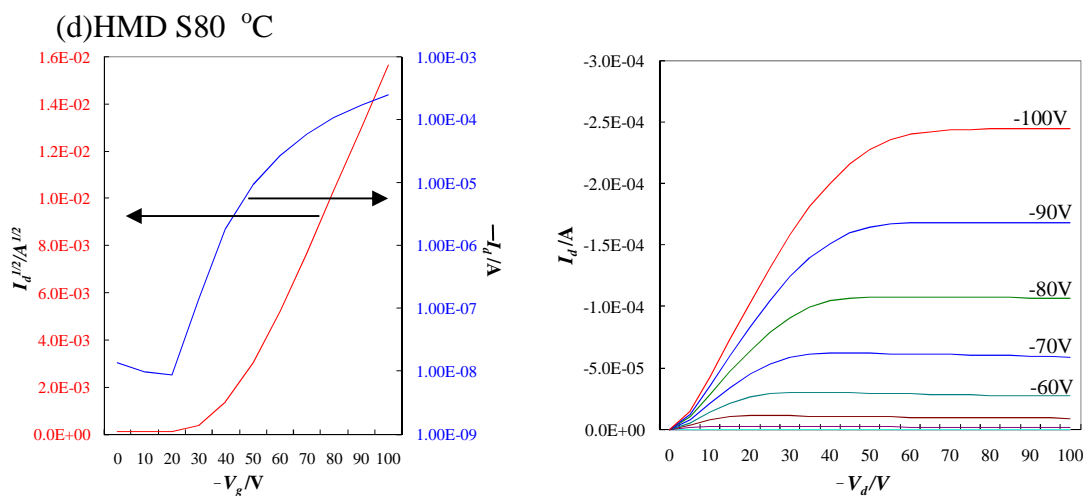


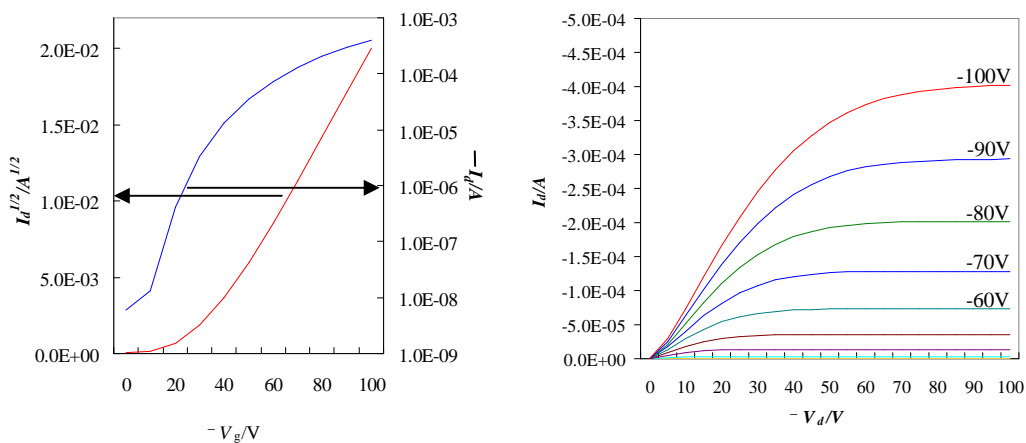
Figure S3. Output and transfer characteristics of the bottom- contact FET devices of **4** deposited on the bare substrate at r.t. (a), HMDS treated substrate at r.t. (b), bare substrate at 80 °C (c) and HMDS treated substrate at 80 °C (d).



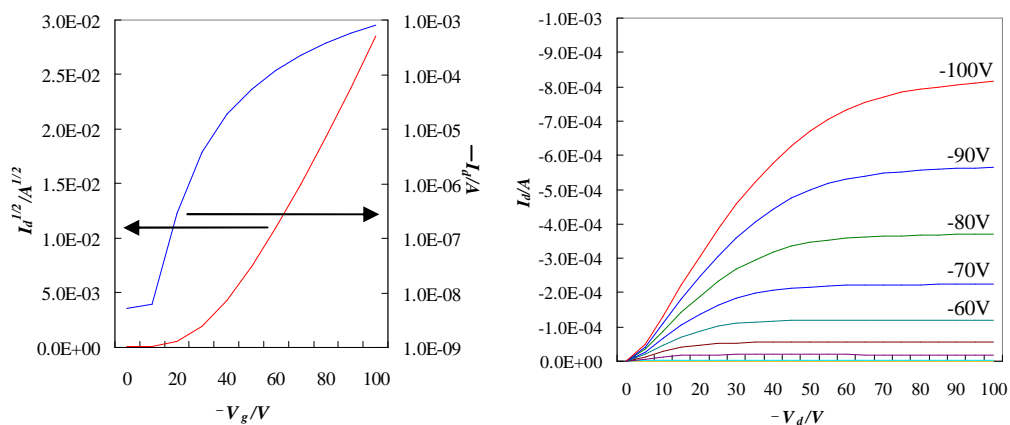


FigureS4. Output and transfer characteristics of the bottom-contact FET devices of 5 deposited on the bare substrate at r.t. (a), HMDS treated substrate at r.t. (b), bare substrate at 80 °C (c), and HMDS treated substrate at 80 °C (d).

(a) Bare r.t.



(b) HMDS r.t.



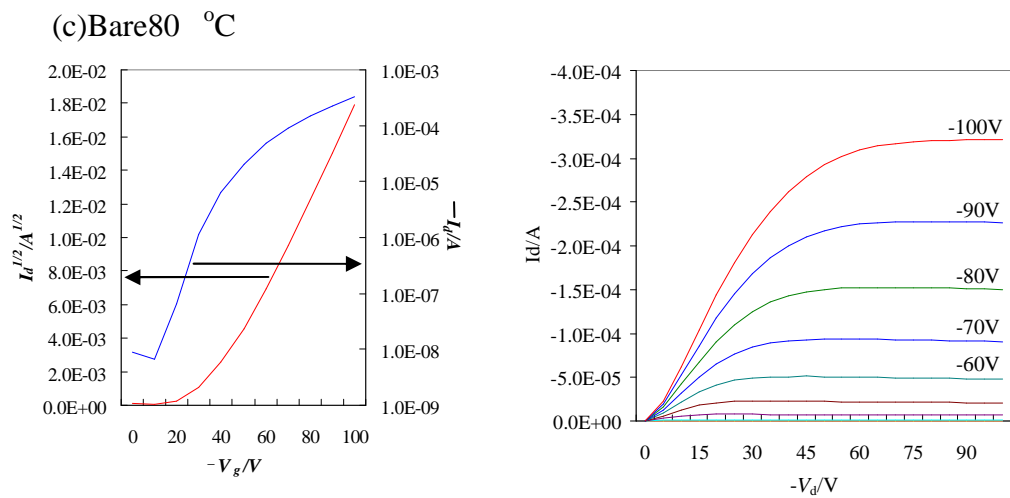


Figure S5. Output and transfer characteristics of the FET devices of **6** deposited on the bare substrate at r.t. (a), HMDS treated substrate at r.t. (b) and bare substrate at 80 °C (c).